

**IN THE CLAIMS:**

Please cancel claim 31 and add new claim 32 as follows:

1. (Previously presented) A method for processing a substrate, comprising:  
providing a substrate comprising a bulk dielectric material disposed on a patterned dielectric material in an amount sufficient to fill feature definitions of the patterned dielectric material;  
polishing the substrate with a first polishing composition and an abrasive-free polishing article until bulk dielectric material is substantially removed; and  
polishing the substrate with a second polishing composition and a fixed-abrasive polishing article to remove residual bulk dielectric material and expose the patterned dielectric material between the feature definitions.
2. (Original) The method of claim 1, wherein the first polishing composition comprises an abrasive-containing polishing composition.
3. (Previously presented) The method of claim 2, wherein the first polishing composition has a removal rate ratio of bulk dielectric material to patterned dielectric material of between about 1:1 and about 5:1.
4. (Previously presented) The method of claim 1, wherein the second polishing composition has a removal rate ratio of bulk dielectric material to patterned dielectric material of about 30:1 or greater.
5. (Original) The method of claim 1, wherein the fixed-abrasive polishing article comprises a high removal rate fixed-abrasive web material.
6. (Original) The method of claim 1, wherein the second polishing composition further contains abrasive particles.

7. (Previously presented) The method of claim 1, further comprising altering the surface of the fixed-abrasive polishing article with a non-mechanical technique selected from the group of applying heat to the polishing article, chemical etching the polishing article, and combinations thereof.

8-24. (Canceled)

25. (Previously presented) A method for processing a substrate, comprising:  
providing a substrate comprising a material layer, an oxide layer disposed over the material layer, a patterned dielectric material disposed on the oxide layer with feature definitions extending through the three layers, and a bulk dielectric material disposed on the patterned dielectric material in a sufficient amount to fill the feature definitions;

polishing the substrate with a first polishing composition and an abrasive-free polishing article until the bulk dielectric material is substantially removed; and

polishing the substrate with a second polishing composition and a fixed-abrasive polishing article to remove residual bulk dielectric material to expose the patterned dielectric material between the feature definitions.

26. (Previously presented) The method of claim 25, wherein the first polishing composition comprises an abrasive-containing polishing composition.

27. (Previously presented) The method of claim 26, wherein the first polishing composition has a removal rate ratio of bulk dielectric material to patterned dielectric material of between about 1:1 and about 5:1.

28. (Previously presented) The method of claim 25, wherein the second polishing composition has a removal rate ratio of bulk dielectric material to patterned dielectric material of about 30:1 or greater.

29. (Previously presented) The method of claim 25, wherein the fixed-abrasive polishing article comprises a high removal rate fixed-abrasive web material.

30. (Previously presented) The method of claim 25, wherein the second polishing composition further contains abrasive particles.

31. (Canceled)

32. (New) A method for processing a substrate, comprising:

providing a substrate comprising a material layer, an oxide layer disposed over the material layer, a patterned dielectric material disposed on the oxide layer with feature definitions extending through the three layers, and a bulk dielectric material disposed on the patterned dielectric material in a sufficient amount to fill the feature definitions;

polishing the substrate with a first polishing composition and an abrasive-free polishing article until the bulk dielectric material is substantially removed; and

polishing the substrate with a second polishing composition and a fixed-abrasive polishing article to remove residual bulk dielectric material to expose the patterned dielectric material between the feature definitions, wherein the bulk dielectric material comprises silicon oxide and the patterned dielectric material comprises silicon nitride.